CDS/AGC & 10-bit A/D Converter

HITACHI

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Description

The HD49323AF-01 is a CMOS IC that provides CCD-AGC analog processing (CDS/AGC) suitable for CCD camera digital signal processing systems together with a 10-bit A/D converter in a single chip.

Functions

- Correlated Double Sampling
- AGC
- Sample hold
- Offset compensation
- Serial interface control
- 10-bit ADC
- 3 V single operation (2.7 V to 3.6 V)
- Power dissipation: 198 mW (Typ)
- Maximum frequency: 20 MHz (Min)

Features

- Good suppression of CCD output low-frequency noise is achieved through the use of S/H type correlated double sampling.
- A high S/N ratio is achieved through the use of a AGC type amplifier, and high sensitivity is provided by a wide cover range.
- An auto offset circuit provides compensation of output DC offset voltage fluctuations due to variations in AGC amplifier gain.
- AGC, standby mode, offset control, etc., is possible via a serial interface.
- High precision is provided by a 10-bit-resolution A/D converter.
- Version of Hitachi's previous-generation HD49322BF with improved functions and performance, including in particular an approximately 3.0 dB improvement in S/N.



Pin Arrangement



Pin Description

Pin No.	Symbol	Description	I/O	Analog(A) or Digital(D)
1	PBLK	Pre-blanking pin	I	D
2	D0	Digital output (LSB)	0	D
3 to 10	D1 to D8	Digital output	0	D
11	D9	Digital output (MSB)	0	D
12	NC	No connection pin	_	_
13	ŌĒ	Digital output enable control pin	Ι	D
14	DV _{ss}	Digital ground (0 V)	_	D
15	DV_{DD}	Digital power supply (3 V) Connect off-chip in common with AV _{DD} .	_	D
16	ADCLK	ADC conversion clock input pin	Ι	D
17	OBP	Optical black pulse input pin	I	D
18	SPBLK	Black level sampling clock input pin	Ι	D
19	SPSIG	Signal level sampling clock input pin	Ι	D
20	AV_{ss}	Analog ground (0 V)	—	А
21	AV_{DD}	Analog power supply (3 V) Connect off-chip in common with DV _{DD} .	—	A
22	NC	No connection pin	—	—
23	CLP	Clamp voltage pin Connect a 0.22 μF or more capacitor between CLP and AV $_{ss}.$		A
24	VRM2	Reference voltage pin (for CCD offset cancel)	_	А
25	AV_{ss}	Analog ground (0 V)	—	А
26	AV_{DD}	Analog power supply (3 V) Connect off-chip in common with DV _{DD} .	—	A
27	CDSIN	CDS input pin	Ι	А
28	TESTY	Test input pin-Y	Ι	А
29	TESTC	Test input pin-C	Ι	А
30	AV_{ss}	Analog ground (0 V)	_	А
31	AV_{DD}	Analog power supply (3 V) Connect off-chip in common with DV _{DD} .		А
32	VRB	Reference voltage pin 3 Connect a 0.1 μF ceramic capacitor between VRB and AV $_{ss}.$	_	A
33	VRM	Reference voltage pin 2 Connect a 0.1 μF ceramic capacitor between VRM and AV $_{ss}.$	_	А
34	VRT	Reference voltage pin 1 Connect a 0.1 μF ceramic capacitor between VRT and AV $_{ss}.$	—	А

Pin Description (cont)

Pin No.	Symbol	Description	I/O	Analog(A) or Digital(D)
35	BIAS	Internal bias pin Connect a 24 $k\Omega$ resistor between BIAS and AV $_{ss}.$	_	A
36	NC	No connection pin	_	_
37	AV _{ss}	Analog ground (0 V)	_	А
38	AV_{DD}	Analog power supply (3 V) Connect off-chip in common with DV _{DD} .	—	A
39, 40	NC	No connection pin	_	
41	AV_{DD}	Analog power supply (3 V) Connect off-chip in common with DV _{DD} .	—	A
42	AV _{ss}	Analog ground (0 V)	_	А
43	CS	Serial interface control input pin	I	D
44	SCK	Serial clock input pin	I	D
45	SDATA	Serial data input pin	I	D
46	DV_{DD}	Digital power supply (3 V) Connect off-chip in common with AV _{DD} .	_	D
47, 48	$\mathrm{DV}_{\mathrm{ss}}$	Digital ground (0 V)	_	D

Input/Output Equivalent Circuit



Note: 1. Applies to \overline{OE} and PBLK.

Block Diagram



Internal Functions

Functional Description

- CDS (Correlated Double Sampling) circuit
- AGC gain selection (11-bit digital control) *¹
 - AGC gain can be set in the range 0 dB to 34.7 dB on the (+) side, and -3.3 dB to 0 dB on the (-) side by means of 11-bit serial data.
- Automatic offset adjustment is possible for the IC's offsets (CDS, AGC, ADC) by means of serial data control at power-on.*¹
- Digital output enable function
- Pre-blanking function
 - Digital output can be fixed at 32 LSB
- CDS offset cancel function

Note: 1. Serial data control

Operating Description

Figure 1 shows CDS/AGC +ADC function block.



Figure 1 CDS/AGC +ADC Function Block

1. CDS (Correlated Double Sampling) Circuit

The CCD imaging element alternately outputs a black level (A-period signal) and a signal including the black level (B-period signal). The CDS circuit extracts the differential voltage between the black level and the signal including the black level (see figure 4).

Black level sampling is performed at the rising edge of the SPBLK pulse, and signal level sampling is performed at the rising edge of the SPSIG pulse. This sequence of operations extracts the differential voltage between the black level and the signal including the black level, and supplies this to the next-stage AGC circuit.

2. Feed back clamp function

The clamp level is set by means of 5-bit serial data. The setting range is 32 LSB to 56 LSB, in 1 LSB steps. A serial data value of 0 gives a 32 LSB setting, and a value of 24 gives a 56 LSB setting.

3. AGC Circuit

The AGC gain is set by means of 11-bit serial data. The setting range is -3.3 dB to 34.7 dB. Details of the data are given in the following section.

The (-) side gain setting uses setting codes -81 to 0 in 0.0039-multiple steps, and the (+) side gain setting uses setting codes 0 to 1023 in 0.034 dB steps.

- Detailed specifications of HD49323AF-01 AGC gain setting codes
 - (1) To improve S/N, the AD input dynamic range has been extended to 1.4 V from the 1.0 V of the HD49322BF.
 - (2) There are two AGC gain ranges: (+) side 0 to 34.7 dB linear gain amp. (0.034 dB/step), and (-) side 0 to -3.3 dB "multiple" linear gain amp. (0.0039 multiple/step).



Considering the case where AGC gain is set so that the ADC output code is 511 when a 150 mV signal is input:

- The HD49322BF AGC gain setting is (code 511)/150 mV multiple = 500 mV/150 mV multiple
- The HD49323AF-01 AGC gain setting is (code 511)/150 mV multiple = 700 mV/150 mV multiple

Code	BIN (D10 to D0)	dB
0	000 0000 0000	0.000
1	000 0000 0001	0.034
2	000 0000 0010	0.068
3	000 0000 0011	0.102
510	001 1111 1110	17.34
511	001 1111 1111	17.37
512	010 0000 0000	17.41
513	010 0000 0001	17.44
1020	011 1111 1100	34.68
1021	011 1111 1101	34.71
1022	011 1111 1110	34.75
1023	011 1111 1111	34.78

Table 1 AGC	Gain (+)	Setting	Code	Table
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Table 2	AGC Gain (-) Settin	ng Code Ta	able
Code	BIN (D10 to D0)	Multiple	dB
0	000 0000 0000	1.000	0.000
-1	111 1111 1111	0.996	-0.034
-2	111 1111 1110	0.992	-0.068
-3	111 1111 1101	0.988	-0.102
-30	111 1110 0010	0.883	-1.083
-31	111 1110 0001	0.879	-1.121
-32	111 1110 0000	0.875	-1.160
-33	111 1101 1111	0.871	-1.199
•			
-78	111 1011 0010	0.695	-3.156
-79	111 1011 0001	0.691	-3.205
-80	111 1011 0000	0.688	-3.255
-81	111 1010 1111	0.684	-3.304

4. Offset cancel circuit

When power is turned on, offset voltages generated by CDS, AGC, ADC, and other circuits by means of serial data control are canceled. (Refer to page 24 (Operating Sequence at Power-On).)

5. Digital output enable function

When the \overline{OE} pin is driven high, digital output goes to the high-Z state.

OE Pin	Digital Output
High	High-Z state
Low (or Open, GND)	Output enable

6. Pre-blanking function

When the PBLK pin is driven high, digital output is fixed at 32 LSB. However, this is valid only when the $\overline{\text{OE}}$ pin and serial data output mode settings (LINV, MINV, TEST, STBY) are low.

PBLK Pin	Digital Output
High	Fixed at 32 LSB
Low (or Open, GND)	Active

7. CCD offset cancel function

This function cancels the offset voltage (V_{OFCCD}) during the optical black period of the CCD imaging element. The definition of the CCD offset voltage (V_{OFCCD}) is given below.

• The difference between the black level sampling voltage and signal level sampling voltage during the OBP period is designated V_{OFCCD}. This value is positive when (signal level sampling voltage) > (black level sampling voltage).



Figure 2 Black Level Signal Level Difference during OBP Period

Table 3Serial Data Settings

V _{OFCCD} Cancel Function	When Used	When Not Used
Serial data settings	VOFCON bit set to 1 VOFD0—3 (4 bits) set	VOFCON bit cleared to 0

- Determining serial set data VOFD0—3
 - (1) Provisional setting Serial data VOFD0—3 settings are made according to the value of V_{OFCCD} as shown in table 4.
 - (2) Actual setting The set data is adjusted so that the CLP pin (pin 23) voltage is closest to 1/2 AV_{DD} when AGC gain is set to the maximum.

The data obtained in (2) is used as the serial set data.

V_{ofccd} **Serial Setting Data** (mV) VOFD3 VOFD2 VOFD1 VOFD0 -110 -90 -70 -50 -30 -10 +10 +30 +50 +70 +90 +110

Table 4 V_{OFCCD} Serial Setting Data Correspondence Table (For Reference)

Timing Chart

Figure 3 shows the output timing.



Figure 3 Output Timing

- The ADC output signals (D0 to D9) are output at the rising edge of ADCLK.
- The pipeline delay is 5 clocks.



Details of Timing Specifications

Details of Timing Specifications

Details of the timing specifications are shown in figure 4, and the timing specifications are summarized in table 5.



Figure 4 Details of Timing Specifications

No.	Timing	Symbol	Min	Тур	Max	Unit	Note
(1)	Black level signal read-in time	t _{CDS1}	0	5	10	ns	1
(2)	SPBLK "Lo" period	t _{CDS2}	11	$1/4f_{ADCLK}$	Typ imes 1.2	ns	2
(3)	Signal level read-in time	t _{CDS3}	0	5	10	ns	1
(4)	SPSIG "Lo" period	t_{CDS4}	11	1/4f _{ADCLK}	Typ imes 1.2	ns	2
(5)	SPBLK rise to SPSIG rise	t _{CDS5}	20	1/2f _{ADCLK}	Typ imes 1.15	ns	2
(6)-1	ADCLK rise to SPBLK rise	t _{CDS6-1}	25		—	ns	2
(6)-2	SPSIG rise to ADCLK rise	t _{CDS6-2}	0			ns	2
(7), (8)	ADCLK t _{wH} Min / t _{wL} Min	t _{CDS7,8}	22			ns	

Table 5 Each Timing Specifications

Note: 1. Negative when data before the rising edge of SPBLK/SPSIG is sampled, and positive when data after the rising edge is sampled.

2. The polarity of SPBLK and SPSIG is for a low setting of the serial data SP INV bit.



Detailed Timing Specifications for Digital Output Enable Control

Detailed timing specifications in the case of digital output enable control are shown in figure 5. When the \overline{OE} pin is high, output disable mode is entered and output goes to the high-Z state.



Figure 5 Detailed Timing Specifications for Digital Output Enable Control

Detailed Timing Specifications for Pre-Blanking

Detailed timing specifications for pre-blanking are shown in figure 6. When the PBLK pin is high, digital output is fixed at 32 LSB. However, the \overline{OE} pin and serial data output mode settings (LINV, MINV, TEST, STBY) take precedence.



Figure 6 Detailed Timing Specifications for Pre-Blanking

Output Code Table

Table 6Function Table

						Digital Output	
OE	STBY	TEST	LINV	MINV	PBLK	D9 D8 D7 D6 D5 D4 D3 D2 D1 D0	Operation Mode
Н	X	Х	Х	Х	Х	Hi-Z	Output Hi-Z
L	Н	X	Х	Х	Х	Hi-Z	Low power standby
	L	L	L	L	L	Table 7 as follows	Normal operation
			L	Н	L	In the table 7 below, D9 is inverted	
			Н	L	L	In the table 7 below, D8 to D0 are inverted	
			Н	н	L	In the table 7 below, D9 to D0 are inverted	
			L	L	Н	LLLLHLHLLLL	Pre-blanking
		Н	L	L	Х	LHLHLHLH	Test mode
			L	н	X	HHLHLHLH	
			Н	L	Х	LLHLHLHLHL	
			Н	Н	Х	HLHLHLHLHL	

Note: 1. STBY, TEST, LINV, and MINV mode setting is performed by means of serial data.

- 2. OE and PBLK mode setting is performed by means of external input pins.
- 3. Pre-blanking mode is enabled when the PBLK pin is high and all other pins are low.

Output Pin		D9	D8	D7	D6	D5	D4	D3	D2	D1	D0	Input Level	
Output	Step	0	L	L	L	L	Ε	L	L	L L	¦ L	L	→0V
code		1	L	L	L	L	L	L	L	L	L	н	l †
		2	L	L	L	L	L	L	L	L	H	L	
		3	L	L	L	L	L	L	L	L	H	н	
		:	÷	:	:	÷	:	:	:	:	:	:	
		511	L	Н	Н	Н	H	Н	Н	H	H	н	→0.7V
		512	Н	L	L	L	L	L	L	L	L	L	
		:	÷	:	:	÷	:	:	:	:	:	:	
		1020	Н	Н	Н	Н	H	Н	Н	H	L	L	
		1021	Н	Н	н	н	H	Н	н	H	L	н	
		1022	Н	Н	н	н	H	Н	Н	H	H	L	
		1023	Н	Н	н	Н	H	Н	Н	Н	H	Н	→1.4V

Table 7Output Code Table

Item	Symbol	Ratings	Unit
Power supply voltage	V _{DD(max)}	6.0	V
Power dissipation	P _{D(max)}	400	mW
Analog input voltage	V _{IN(max)}	-0.3 to AV _{DD} +0.3	V
Digital input voltage	V _{I(max)}	-0.3 to 6.0	V
Operating temperature	Topr	-10 to +85	°C
Storage temperature	Tstg	–55 to +125	°C

Absolute Maximum Ratings $(Ta = 25^{\circ}C)$

Note: 1. V_{DD} indicates AV_{DD} and DV_{DD} .

 Common connection of AV_{DD} and DV_{DD} should be made off-chip. If AV_{DD} and DV_{DD} are isolated by a noise filter, the phase difference should be 0.3 V or less at power-on and 0.1 V or less during operation.

ltem	Symbol	Min	Тур	Max	Unit	Test Conditions	Remarks
Power supply voltage range	V_{DD}	2.70	3.00	3.60	V	f _{CLK} = 20 MHz	
Conversion	f _{CLK} max	20	_	_	MHz		
frequency	f _{CLK} min	_	_	5.5	MHz		
Digital input voltage	V _{IH}	$2.0 imes rac{DV_{DD}}{3.0}$	_	5.0	V		5 V amplitude input possible
	V _{IL}	0	_	$0.8 imes rac{DV_{DD}}{3.0}$	V		Digital input pins except CS, SCK, and SDATA
	V _{IH2}	$2.25 \times \frac{DV_{DD}}{3.0}$	_	5.0	V		5 V amplitude input possible
	V _{IL2}	0	_	$0.6 imes rac{DV_{DD}}{3.0}$	V		CS, SCK, SDATA
Digital output	V _{OH}	DV _{DD} -0.5	_	_	V	I _{он} = –2 mА	
voltage	V _{OL}	—	_	0.5	V	$I_{OL} = +2 \text{ mA}$	
Digital input current	I _{IH}	_	_	50	μΑ	V _{IH} = 5.0 V	Digital input pins except PBLK and OE
	I _{IH2}	—	_	250	μA	V _{IH} = 5.0 V	PBLK, \overline{OE}
	I _{IL}	-50	—	_	μA	$V_{IL} = 0 V$	
Digital output	I _{OZH}	—	_	50	μA	$V_{OH} = V_{DD}$	
current	I _{OZL}	-50	_	_	μA	$V_{OL} = 0 V$	
ADC resolution	RES	10	10	10	bit		
ADC integration linearity error	INL	_	4	10	LSBp-p	f _{CLK} = 20 MHz	
ADC differentiation	DNL+	_	0.3	0.8	LSB	f _{CLK} = 20 MHz	*1
linearity error	DNL-	-0.8	-0.3	_	LSB	-	
Digital output delay time	t _{PD}			35	ns	C _L = 10 pF	
Digital output hold time	t _{HOLD}	10	_	_	ns	-	

Electrical Characteristics (Unless othewide specified, $Ta = 25^{\circ}C$, $AV_{DD} = 3.0 V$, $DV_{DD} = 3.0 V$, $R_{EXT} = 24 k\Omega$)

Note: 1. DNL calculate the difference of linearity error between next two codes.

Electrical Characteristics (Unless othewide specified, $Ta = 25^{\circ}C$, $AV_{DD} = 3.0 V$, $DV_{DD} = 3.0 V$, $R_{EXT} = 24 \text{ k}\Omega$) (cont)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions	Remarks
Sleep current	I _{SLP}	-100	0	100	μΑ	Digital input pins fixed at 0 V, output pins open	
Standby current	I _{stby}	—	8	12	mA	Digital input pins fixed at 0 V	
ADC Input range	V _{INp-p}	_	(1.4)	_	V		*2
Digital output Hi-Z	t _{HZ}	_	_	100	ns	$R_L = 2 k\Omega$	*3
delay time	t _{LZ}	_	_	100	ns	C _L = 10 pF	
	t _{zH}	—	—	100	ns		
	t _{zL}	_	_	100	ns	-	
Digital output PBLK delay time	t _{PBLK}	—	—	100	ns	C _L = 10 pF	*3
Quiescent current	I _{DD1}	_	66	78	mA	f _{CLK} = 20 MHz	CDSIN use
Timing specification (1)	t _{CDS1}	0	5	10	ns		*3
Timing specification (2)	t _{CDS2}	11	1/4f _{ADCLK}	$\text{Typ}\times 1.2$	ns		-
Timing specification (3)	t _{CDS3}	0	5	10	ns		-
Timing specification (4)	t _{CDS4}	11	1/4f _{ADCLK}	$\text{Typ}\times 1.2$	ns		-
Timing specification (5)	t _{CDS5}	20	1/2f _{ADCLK}	Typ imes 1.15	ns		-
Timing specification (6-1)	t _{CDS6-1}	25	_	_	ns		-
Timing specification (6-2)	t _{CDS6-2}	0	_	_	ns		-
Timing specification (7)	t _{CDS7}	22	—	—	ns		-
Timing specification (8)	t _{CDS8}	22	_	_	ns		-
Input current	IIN _{CDS}	-60	_	10	μΑ	$f_{CLK} = 20 \text{ MHz},$ Black/signal level difference = 1 V, gain = 0 dB	*4
Clamp level	CLP(00)	_	(32)	_	LSB		*2
	CLP(16)		(48)	_	LSB		_
	CLP(24)	_	(56)		LSB		

Note: 2. Items in parentheses are reference values.

3. Refer to page 12 (Details of Timing Specifications).

4. This is not transition current, but static current.

ltem	Symbol	Min	Тур	Max	Unit	Test Conditions	Remarks
AGC gain(-)	AGC(-081)	-5.3	-3.3	-1.3	dB		
	AGC(0000)	-2.0	0	2.0	dB		
AGC gain(+)	AGC(0000)	-2.0	0	2.0	dB		
	AGC(0128)	2.4	4.4	6.4	dB		
	AGC(0256)	6.7	8.7	10.7	dB		_
	AGC(0384)	11.1	13.1	15.1	dB		
	AGC(0512)	15.4	17.4	19.4	dB		
	AGC(0640)	19.8	21.8	23.8	dB		_
	AGC(0768)	24.1	26.1	28.1	dB		
	AGC(0896)	28.5	30.5	32.5	dB		_
	AGC(1023)	32.3	34.8	37.8	dB		_

Electrical Characteristics (Unless othewide specified, Ta = 25°C, $AV_{DD} = 3.0 \text{ V}$, $DV_{DD} = 3.0 \text{ V}$, $R_{EXT} = 24 \text{ k}\Omega$) (cont)

Serial Interface Specification



Figure 7 Serial Interface Specification

	Resister 0	Resister 1	Resister 2	Resister 3
DI 00 (LSB)	Lo	Hi	Lo	Hi
DI 01	Lo	Lo	Hi	Hi
DI 02	AGC Gain setting (LSB)	SP INV SPSIG/SPBLK inversion	Clamp level adjustment (LSB)	
DI 03	AGC Gain setting	OBP INV Lo→Negative input Hi→Positive input	Clamp level adjustment	
DI 04	AGC Gain setting	$\begin{array}{c} {\sf CIF} \qquad \begin{array}{c} {\sf Lo} {\rightarrow} {\sf f}_{{\sf CLK}} {\succ} 10 {\sf MHz} \\ {\sf Hi} {\rightarrow} {\sf f}_{{\sf CLK}} {<} 10 {\sf MHz} \end{array}$	Clamp level adjustment	
DI 05	AGC Gain setting	VOFCON Lo \rightarrow OFF * ³ Hi \rightarrow ON	Clamp level adjustment	
DI 06	AGC Gain setting	VOFD0 (LSB) CCD offset voltage setting	Clamp level adjustment (MSB)	
DI 07	AGC Gain setting	VOFD1 CCD offset voltage setting	Test mode *2 Low	
DI 08	AGC Gain setting	VOFD2 CCD offset voltage setting	Low	Test mode *2
DI 09	AGC Gain setting	VOFD3 (MSB) CCD offset voltage setting	Low	ALL Low
DI 10	AGC Gain setting	Output mode setting (LINV)	Low	
DI 11	AGC Gain setting	Output mode setting (MINV)	High	
DI 12	AGC Gain setting (MSB)	Output mode setting (TEST)	Low	
DI 13	Test mode Low setting *2	RESET Lo→Reset mode Hi→Normal operation mode	High	
DI 14	Test mode Low setting *2	OFRST Lo→Normal operation mode Hi→Offset cancel mode	High	
DI 15 (MSB)	Output mode setting (STBY) *1	SLP Lo→Normal operation mode *1 Hi→Sleep mode	High	

Table 8 **Serial Data Functions Table**

Notes: 1. STBY: Reference voltage generation circuit is in the operational state.

SLP: All circuits are in the sleep state.

Test mode is used for IC testing, and so cannot be used.
 Register 2 test mode should be set in accordance with the specification at the right of the column.

For other registers, the setting should only be made in the all-low state. 3. Setting of VOFCON: Lo \rightarrow CCD offset cancel function OFF

: Hi -> CCD offset cancel function ON

Timing Specifications

3 - 1								
	Min	Max						
f _{SCK}	—	3MHz						
t _{INT} 1, 2	50ns							
t _{su}	50ns							
t _{ho}	50ns							

• OBP polarity



Notice for Use

- 1. Careful handling is necessary to prevent damage due to static electricity.
- This product has been developed for consumer applications, and should not be used in non-consumer applications.
- 3. As this IC is sensitive to power line noise, the ground impedance should be kept as small as possible. Also, to prevent latchup, a ceramic capacitor of 0.1 μ F or more and an electrolytic capacitor of 10 μ F or more should be inserted between the ground and power supply.
- Common connection of AV_{DD} and DV_{DD} should be made off-chip. If AV_{DD} and DV_{DD} are isolated by a noise filter, the phase difference should be 0.3 V or less at power-on and 0.1 V or less during operation.
- 5. If a noise filter is necessary, make a common connection after passage through the filter, as shown in the figure below.



- 6. Connect AV_{ss} and DV_{ss} off-chip using a common ground. If there are separate analog system and digital system set grounds, connect to the analog system.
- 7. When V_{DD} is specified in the delivery specification, this indicates AV_{DD} and DV_{DD} .
- 8. No Connection (NC) pins are not connected inside the IC, but it is recommended that they be used as power supply ground pins or left open to prevent crosstalk in adjacent analog pins.
- 9. To ensure low thermal resistance of the package, a Cu-type lead material is used. As this material is less tolerant of bending than Fe-type lead material, careful handling is necessary.
- 10. The infrared reflow soldering method should be used to mount the chip. Note that general heating methods such as solder dipping cannot be used.
- 11. Depending on the mounting state, picture quality (crosscut noise, wave pattern, etc.) will be dependent upon the timing of the SPBLK, SPSIG, and ADCLK signals. Check the mounting state thoroughly before use.
- 12. Serial communication should not be performed during the effective video period, since this will result in degraded picture quality. Also, use of dedicated ports is recommended for the SCK and SDATA signals used in the HD49323AF-01. If ports are to be shared with another IC, picture quality should first be thoroughly checked.
- 13. At power-on, automatic adjustment of the offset voltage generated from CDS, AGC, ADC, etc., must be implemented in accordance with the power-on operating sequence (see page 24).

- 14. If the phase difference between the black level sampling voltage and the signal level sampling voltage during the CCD imaging element optical black period (the CCD offset voltage) is ±30 mV or greater, the CCD offset cancel function (page 9, item 7, CCD Offset Cancel Function) must be implemented. The CCD offset voltage variation after implementation of the CCD offset cancel function should be within ±20 mV.
- 15. The CDSIN pin is clamped at VRM ($\cong AV_{DD}/2$) during operation. The IC may suffer permanent damage if used with a pin voltage in the range -0.3 V to $AV_{DD} + 0.3$ V. Careful attention must therefore be paid to the input signals.

Operating Sequence at Power-On



Figure 8 Operating Sequence at Power-On

Serial data transmission contents are shown in table 9.

"X" indicates data for which the clock polarity, clamp level, etc., can be selected. See page 21 (table 8, Serial Data Functions Table) for the purpose of the data.

Table 9Serial Data

		MSB Serial Data (DI)									LSB							
Order of Transfer		15	14	13	12	11	10	09	08	07	06	05	04	03	02	01	00	Remarks
(1) RESET = "Lo"	a)	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1	
(2) RESET = "Hi"	b)	0	0	1	0	0	0	0	0	0	0	0	0	0	0	0	1	
(3) Data transfer	c)	0	0	1	0	0	0	Х	Х	Х	Х	Х	Х	Х	Х	0	1	
	d)	1	1	1	0	1	0	0	0	0	Х	Х	Х	Х	Х	1	0	
Wait																		1 V (16 ms) or more
(4) OFRST = "Hi"	e)	0	1	1	0	0	0	Х	Х	Х	Х	Х	Х	Х	Х	0	1	
Wait																		4 V (64 ms) or more
(5) OFRST = "Lo"	f)	0	0	1	0	0	0	Х	Х	Х	Х	Х	Х	Х	Х	0	1	
(6) Data transfer	g)	0	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	0	0	

Example of Recommended External Circuit



Package Dimensions



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